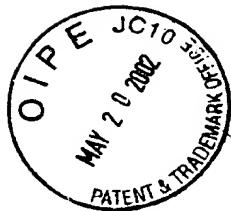


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RESPONSE UNDER 37 CFR 1.116
EXPEDITED PROCEDURE
EXAMINING GROUP 2811

PATENT APPLICATION
Do. No. 5484-48

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Byung-Sup SHIM, et al.

Serial No. 09/305,240

Examiner: Nadav. Ori

Filed: May 4, 1999

Group Art Unit: 2811

For: **OPEN DRAIN INPUT/OUTPUT STRUCTURE AND MANUFACTURING
METHOD THEREOF IN SEMICONDUCTOR DEVICE**

BOX AF

Assistant Commissioner for Patents
Washington, D.C. 20231

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AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR 1.116

Responsive to the Final Office Action , dated of February 13, 2002 and Advisory Action, dated April 19, 2002, please amend the application as follows.

IN THE CLAIMS

- E1
WMS R1
5. (Twice Amended) A pull-up transistor disposed between a Vdd terminal and an I/O pad of a semiconductor device comprising:
a semiconductor substrate of a first conductive-type;
a source region and a drain region of a second conductive type formed in the substrate and defining between them a channel region, one of the source region and the drain region being electrically coupled to the I/O pad, the other one of the source region and the drain region being electrically coupled to the Vdd terminal;
an impurity implantation region of impurities of a second conductive-type formed in a first sector of the channel region, the first sector not reaching either one of the source region and the drain region;
the impurity implantation region of the first sector comprising a surface region operable under field effect as a depletion channel;